Bo E Sernelius

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

176	4,822	32	67
papers	citations	h-index	g-index
191	5,204	2.6	5.66
ext. papers	ext. citations	avg, IF	L-index

#	Paper	IF	Citations
176	Heavily n-doped Ge: Low-temperature magnetoresistance properties on the metallic side of the metal‐nonmetal transition. *Journal of Applied Physics*, **2020**, 127, 045705	2.5	0
175	Fundamentals of van der Waals and Casimir Interactions. *Springer Series on Atomic, Optical, and Plasma Physics*, **2018**,	0.4	5
174	Van der Waals Interaction in Spherical Structures. *Springer Series on Atomic, Optical, and Plasma Physics*, **2018**, 209-232	0.4	
173	Van der Waals Interaction in Cylindrical Structures. *Springer Series on Atomic, Optical, and Plasma Physics*, **2018**, 233-255	0.4	
172	Casimir Interaction. *Springer Series on Atomic, Optical, and Plasma Physics*, **2018**, 259-271	0.4	
171	Dispersion Interaction in Planar Structures. *Springer Series on Atomic, Optical, and Plasma Physics*, **2018**, 273-337	0.4	
170	Dispersion Interaction in Spherical Structures. *Springer Series on Atomic, Optical, and Plasma Physics*, **2018**, 339-371	0.4	
169	Dispersion Interaction in Cylindrical Structures. *Springer Series on Atomic, Optical, and Plasma Physics*, **2018**, 373-392	0.4	
168	Statistical Physics. *Springer Series on Atomic, Optical, and Plasma Physics*, **2018**, 61-68	0.4	
167	Electromagnetic Normal Modes. *Springer Series on Atomic, Optical, and Plasma Physics*, **2018**, 69-107	0.4	
166	Different Approaches. *Springer Series on Atomic, Optical, and Plasma Physics*, **2018**, 109-123	0.4	
165	General Method to Find the Normal Modes in Layered Structures. *Springer Series on Atomic, Optical, and Plasma Physics*, **2018**, 125-131	0.4	
164	Van der Waals Force. *Springer Series on Atomic, Optical, and Plasma Physics*, **2018**, 135-151	0.4	
163	Van der Waals Interaction in Planar Structures. *Springer Series on Atomic, Optical, and Plasma Physics*, **2018**, 153-207	0.4	
162	Core-level spectra from bilayer graphene. *FlatChem*, **2017**, 1, 6-10	5.1	1
161	Non-perturbative theory of dispersion interactions. *Physica Scripta*, **2015**, 90, 035405	2.6	1
160	Casimir effects in systems containing 2D layers such as graphene and 2D electron gases. *Journal of Physics Condensed Matter*, **2015**, 27, 214017	1.8	15

159	Magnetoresistance of doped silicon. *Physical Review B*, **2015**, 91,	3.3	4
158	Relativistic Doppler reflection as a probe for the initial relaxation of a non-equilibrium electron-hole plasma in silicon. *Journal of Physics: Conference Series*, **2015**, 647, 012016	0.3	0
157	Core-level spectra from graphene. *Physical Review B*, **2015**, 91,	3.3	13
156	Ultrafast dynamic conductivity and scattering rate saturation of photoexcited charge carriers in silicon investigated with a midinfrared continuum probe. *Physical Review B*, **2015**, 91,	3.3	11
155	Nonperturbative theory for the dispersion self-energy of atoms. *Physical Review A*, **2014**, 90,	2.6	2
154	Finite-size￾dependent dispersion potentials between atoms and ions dissolved in water. *Europhysics Letters*, **2014**, 106, 53002	1.6	1
153	Casimir forces in a plasma: possible connections to Yukawa potentials. *European Physical Journal D*, **2014**, 68, 1	1.3	6
152	Electromagnetic normal modes and Casimir effects in layered structures. *Physical Review B*, **2014**, 90,	3.3	11
151	Two approaches for describing the Casimir interaction in graphene: Density-density correlation function versus polarization tensor. *Physical Review B*, **2014**, 89,	3.3	52
150	Intermolecular Casimir-Polder forces in water and near surfaces. *Physical Review E*, **2014**, 90, 032122	2.4	8
149	Casimir force between atomically thin gold films. *European Physical Journal B*, **2013**, 86, 1	1.2	14
148	Resonance interaction induced by metal surfaces catalyzes atom-pair breakage. *Physical Review A*, **2013**, 87,	2.6	2
147	Lithium atom storage in nanoporous cellulose via surface-induced Li 2 breakage. *Europhysics Letters* , **2013**, 104, 63003	1.6	2
146	Atmospheric water droplets can catalyse atom pair break-up via surface-induced resonance repulsion. *Europhysics Letters*, **2013**, 101, 43002	1.6	1
145	Sign of the Casimir-Polder interaction between atoms and oil-water interfaces: Subtle dependence on dielectric properties. *Physical Review A*, **2012**, 85,	2.6	5
144	Casimir attractive-repulsive transition in MEMS. *European Physical Journal B*, **2012**, 85, 1	1.2	12
143	Retarded interactions in graphene systems. *Physical Review B*, **2012**, 85,	3.3	74
142	CASIMIR EFFECTS IN GRAPHENE SYSTEMS: UNEXPECTED POWER LAWS. *International Journal of Modern Physics Conference Series*, **2012**, 14, 531-540	0.7	5

141	Casimir-Lifshitz interaction between ZnO and SiO2 nanorods in bromobenzene turns repulsive at intermediate separations due to retardation effects. *Physical Review A*, **2012**, 85,	2.6	3
140	Ultrathin metallic coatings can induce quantum levitation between nanosurfaces. *Applied Physics Letters*, **2012**, 100, 253104	3.4	10
139	Enlarged molecules from excited atoms in nanochannels. *Physical Review A*, **2012**, 86,	2.6	4
138	Repulsive van der Waals forces due to hydrogen exposure on bilayer graphene. *Physical Review A*, **2012**, 85,	2.6	21
137	Retardation turns the van der Waals attraction into a Casimir repulsion as close as 3 nm. *Physical Review A*, **2012**, 85,	2.6	26
136	Graphene as a Strictly 2D Sheet or as a Film of Small but Finite Thickness. *Graphene*, **2012**, 01, 21-25	1.5	11
135	Casimir interactions in graphene systems. *Europhysics Letters*, **2011**, 95, 57003	1.6	65
134	Attractive double-layer forces between neutral hydrophobic and neutral hydrophilic surfaces. *Physical Review E*, **2011**, 84, 061903	2.4	8
133	Phonon replicas of charged and neutral exciton complexes in single quantum dots. *Physical Review B*, **2010**, 82,	3.3	7
132	THE THERMAL CASIMIR EFFECT: SATURATION. *International Journal of Modern Physics A*, **2010**, 25, 2319-2327	1.2	1
131	Casimir experiments showing saturation effects. *Physical Review A*, **2009**, 80,	2.6	10
130	GRAVITATION AS A CASIMIR EFFECT. *International Journal of Modern Physics A*, **2009**, 24, 1804-1812	1.2	2
129	Saturation effects in experiments on the thermal Casimir effect. *Europhysics Letters*, **2009**, 87, 14004	1.6	2
128	Free electron behavior in InN: On the role of dislocations and surface electron accumulation. *Applied Physics Letters*, **2009**, 94, 022109	3.4	38
127	Test of the Proximity Force Approximation. *Journal of Physics: Conference Series*, **2009**, 161, 012016	0.3	5
126	Surface recombination in ZnO nanorods grown by chemical bath deposition. *Journal of Applied Physics*, **2008**, 104, 073526	2.5	67
125	Numerical study of the effect of structure and geometry on van der Waals forces. *Journal of Physics A: Mathematical and Theoretical*, **2008**, 41, 164008	2	3
124	The energy spectrum of electromagnetic normal modes in dissipative media: modes between two metal half spaces. *Journal of Physics A: Mathematical and Theoretical*, **2008**, 41, 164016	2	2

(2005-2008)

123	Beyond the simple proximity force approximation: Geometrical effects on the nonretarded Casimir interaction. *Physical Review A*, **2008**, 78,	2.6	11
122	Electric dipole polarizabilities and C6 dipole-dipole dispersion coefficients for alkali metal clusters and C60. *Journal of Computational Methods in Sciences and Engineering*, **2008**, 7, 475-488	0.3	1
121	Forces between air-bubbles in electrolyte solution. *Chemical Physics Letters*, **2008**, 458, 299-302	2.5	8
120	Defect related issues in the “current roll-off” in InGaN based light emitting diodes. *Applied Physics Letters*, **2007**, 91, 181103	3.4	248
119	Reply to “Comment on ‘Effects of spatial dispersion on electromagnetic surface modes and on modes associated with a gap between two half spaces’” *Physical Review B*, **2007**, 75,	3.3	2
118	Metal-insulator transition and superconductivity in boron-doped diamond. *Physical Review B*, **2007**, 75,	3.3	151
117	Electric dipole polarizabilities and C6 dipole-dipole dispersion coefficients for sodium clusters and C60. *Journal of Chemical Physics*, **2006**, 125, 124306	3.9	34
116	Casimir force and complications in the van Kampen theory for dissipative systems. *Physical Review B*, **2006**, 74,	3.3	17
115	Electrical resistivity and metal-nonmetal transition in n-type doped 4H–SiC. *Physical Review B*, **2006**, 74,	3.3	23
114	Finite-temperature Casimir force between metal plates: full inclusion of spatial dispersion resolves a long-standing controversy. *Journal of Physics A*, **2006**, 39, 6741-6752		24
113	CAN THE RADIATION FROM CELLULAR PHONES HAVE IMPORTANT EFFECTS ON THE FORCES BETWEEN BIOLOGICALTISSUE-COMPONENTS? **2006**, 355-366		
112	Colloids **2005**, 317-360		
111	Appendix 2: Fourier-Transform Conventions **2005**, 363-363		
110	Forces **2005**, 167-196		
109	Appendix 1: Conversion Table from CGS to SI Units **2005**, 361-361		
108	Different mode types **2005**, 285-315		
107	Zero-point energy of modes **2005**, 79-97		
106	Energy and force **2005**, 197-255		

105	Bulk modes **2005**, 17-29		
104	Model dielectric functions **2005**, 31-77		
103	Modes at non-planar interfaces **2005**, 257-284		
102	Effects of spatial dispersion on electromagnetic surface modes and on modes associated with a gap between two half spaces. *Physical Review B*, **2005**, 71,	3.3	63
101	Modes at flat interfaces **2005**, 99-165		
100	Complex polarization propagator method for calculation of dispersion coefficients of extended pi-conjugated systems: the C6 coefficients of polyacenes and C60. *Journal of Chemical Physics*, **2005** , 123, 124312	3.9	31
99	First principle calculations of dipole-dipole dispersion coefficients for the ground and first ππ* excited states of some azabenzenes. *Journal of Computational Methods in Sciences and Engineering*, **2004**, 4, 321-332	0.3	9
98	C6 dipole-dipole dispersion coefficients for the n-alkanes: Test of an additivity procedure. *Physical Review A*, **2004**, 69,	2.6	20
97	Photoluminescence study of Si-doped GaNAl0.07Ga0.93N multiple quantum wells with different dopant position. *Applied Physics Letters*, **2004**, 84, 5071-5073	3.4	11
96	Electrical resistivity of acceptor carbon in GaAs. *Journal of Applied Physics*, **2004**, 95, 2532-2535	2.5	10
95	Entropy of the Casimir effect between real metal plates. *Physica A: Statistical Mechanics and Its Applications*, **2004**, 339, 53-59	3.3	52
94	Reply to the "Comment on "Possible induced enhancement of dispersion forces by cellular phones"" by R. K. Adair, Phys. Chem. Chem. Phys., 2004, 6, DOI: 10.1039/b405698a. *Physical Chemistry Chemical Physics*, **2004**, 6, 3916-3916	3.6	
93	Reply to the "Comment on "Possible induced enhancement of dispersion forces by cellular phones"" by Q. Balzano, Phys. Chem. Chem. Phys., 2004, 6, DOI: 10.1039/b406111j. *Physical Chemistry Chemical Physics*, **2004**, 6, 3918-3918	3.6	
92	Possible induced enhancement of dispersion forces by cellular phones. *Physical Chemistry Chemical Physics*, **2004**, 6, 1363-1368	3.6	9
91	Comment on "Possible induced enhancement of dispersion forces by cellular phones" by B. E. Sernelius, Phys. Chem. Chem. Phys., 2004, 6, 1363. *Physical Chemistry Chemical Physics*, **2004**, 6, 3915-3915	3.6	2
90	Optical absorption of Li-intercalated polycrystalline tungsten oxide films: comparison to large polaron theory. *Solid State Ionics*, **2003**, 165, 35-41	3.3	43
89	Polarization propagator calculations of the polarizability tensor at imaginary frequencies and long-range interactions for the noble gases and n-alkanes. *Journal of Chemical Physics*, **2003**, 118, 9167-9174	3.9	46
88	Electrical resistivity, MNM transition and band-gap narrowing of cubic GaN:Si. *Microelectronics Journal*, **2002**, 33, 365-369	1.8	5

87	Acoustic-phonon anomaly in MgB2. *Physical Review B*, **2002**, 66,	3.3	8
86	Optical and reduced band gap in n- and p-type GaN and AlN. *Journal of Applied Physics*, **2002**, 92, 3207-3216	2.5	15
85	Strong enhancement of dispersion forces from microwave radiation. *Europhysics Letters*, **2002**, 60, 643-648	1.6	4
84	Electrical resistivity and band-gap shift of Si-doped GaN and metal-nonmetal transition in cubic GaN, InN and AlN systems. *Journal of Crystal Growth*, **2001**, 231, 420-427	1.6	10
83	Effective electron and hole masses in intrinsic and heavily n-type doped GaN and AlN. *Journal of Physics Condensed Matter*, **2001**, 13, 8915-8922	1.8	18
82	Influence of Si doping on optical properties of wurtzite GaN. *Journal of Physics Condensed Matter*, **2001**, 13, 8891-8899	1.8	8
81	Comment on "Casimir force at both nonzero temperature and finite conductivity". *Physical Review Letters*, **2001**, 87, 259101	7.4	21
80	Sernelius Replies:. *Physical Review Letters*, **2001**, 87,	7.4	17
79	**2001**,		137
78	Plasma-induced band edge shifts in 3C-, 2H-, 4H-, 6H-SiC and Si. *Solid-State Electronics*, **2000**, 44, 471-476	1.7	17
77	Temperature effects on the Casimir attraction between a pair of quantum wells. *Microelectronic Engineering*, **2000**, 51-52, 287-297	2.5	12
76	Many-body effects in highly p-type modulation-doped GaAs/AlxGa1-xAs quantum wells. *Physical Review B*, **2000**, 61, 2794-2798	3.3	9
75	Retardation-enhanced van der Waals force between thin metal films. *Physical Review B*, **2000**, 62, 7523-7526	3.3	10
74	Thermal effects on the casimir force in the 0.1- 5 &mgr;m range. *Physical Review Letters*, **2000**, 84, 4757-60	7.4	243
73	Comment on "Calculation of the Casimir force between imperfectly conducting plates" *Physical Review A*, **2000**, 61,	2.6	20
72	Band-gap shift of the heavily doped single- and double-donor systems Si:Bi and Si:P,Bi. *Physical Review B*, **2000**, 62, 12882-12887	3.3	8
71	Fractional van der Waals interaction between thin metallic films. *Physical Review B*, **2000**, 61, 2204-2210	3.3	71
70	van der Waals energy of an atom in the proximity of thin metal films. *Physical Review A*, **2000**, 61,	2.6	22

69	Impurity resistivity of the double-donor system Si:P,Bi. *Physical Review B*, **1999**, 60, 15824-15828	3.3	16
68	Band gap narrowing in n-type and p-type 3C-, 2H-, 4H-, 6H-SiC, and Si. *Journal of Applied Physics*, **1999**, 86, 4419-4427	2.5	69
67	Optical properties of doped InGaN/GaN multiquantum-well structures. *Applied Physics Letters*, **1999** , 74, 3299-3301	3.4	48
66	Wetting problems for coatings on windshields. *Applied Surface Science*, **1999**, 142, 375-380	6.7	7
65	Doping-induced effects on the band structure in n-type 3C-2H-4H-6H-SiC, and Si. *Physical Review B*, **1999**, 60, 16479-16493	3.3	49
64	Effects of van der Waals Interaction on Current Drag between Quantum Wells. *Physica Scripta*, **1999**, T79, 89	2.6	2
63	Carrier and exciton dynamics in In0.15Ga0.85 NGaN multiple quantum well structures **1999**,		4
62	Mechanism for Radiative Recombination in In0.15Ga0.85N/GaN Multiple Quantum Well Structures. *MRS Internet Journal of Nitride Semiconductor Research*, **1999**, 4, 87-92		0
61	Properties of Si δ-layers embedded in GaAs. *Physica E: Low-Dimensional Systems and Nanostructures* , **1998**, 2, 247-251	3	
60	Many-body effects in highly acceptor-doped GaAs/AlxGa1−xAs quantum wells. *Physical Review B*, **1998**, 58, 4624-4628	3.3	10
59	Si δ-layers embedded in GaAs. *Applied Physics Letters*, **1998**, 73, 3709-3711	3.4	1
58	Interaction energy for a pair of quantum wells. *Physical Review B*, **1998**, 57, 6592-6601	3.3	45
57	Influence of potential fluctuations on electrical transport and optical properties in modulation-doped GaN/Al0.28Ga0.72N heterostructures. *Physical Review B*, **1998**, 58, 1442-1450	3.3	12
56	Mechanism for Radiative Recombination in In0.15Ga0.85N/GaN Multiple Quantum Well Structures. *Materials Research Society Symposia Proceedings*, **1998**, 537, 1		1
55	Transport properties of silicon implanted with bismuth. *Physical Review B*, **1997**, 55, 9584-9589	3.3	17
54	Metal-nonmetal transition and resistivity of silicon implanted with bismuth. *Journal of Materials Research*, **1997**, 12, 641-645	2.5	9
53	Evidence of Potential Fluctuations in Modulation Doped GaN/AlGaN Heterostructures. *Materials Research Society Symposia Proceedings*, **1997**, 482, 623		2
52	Impurity resistivity in doubly-doped systems. *Physica Scripta*, **1997**, T69, 286-289	2.6	

51	Current drag in a single quantum well. *Journal of Physics Condensed Matter*, **1996**, 8, 3705-3714	1.8	2
50	Plasmon shake-up effects in quantum-well exciton spectra. *Journal of Physics Condensed Matter*, **1996**, 8, 9071-9081	1.8	2
49	Optical and transport studies of highly acceptor doped GaAs/AlGaAs quantum wells. *Surface Science*, **1996**, 361-362, 420-423	1.8	1
48	Optical studies of acceptor centre doped quantum wells. *Solid-State Electronics*, **1996**, 40, 89-92	1.7	1
47	Excitation-induced optical switching in transparent coatings. *Thin Solid Films*, **1996**, 278, 104-107	2.2	
46	Exciton properties in p-type GaAs/AlxGa1-xAs quantum wells in the high doping regime. *Physical Review B*, **1996**, 54, 16989-16993	3.3	14
45	Thermally activated intersubband and hopping transport in center-doped p-type GaAs/AlxGa1-xAs quantum wells. *Physical Review B*, **1996**, 53, 1357-1361	3.3	9
44	Electrical resistivity of bismuth implanted into silicon. *Journal of Applied Physics*, **1996**, 79, 3453-3455	2.5	6
43	Spectroscopy studies of highly acceptor doped GaAs/AlGaAs quantum wells. *Superlattices and Microstructures*, **1995**, 18, 153-155	2.8	2
42	Electron mobility enhancement in Si using doubly □-doped layers. *Applied Physics Letters*, **1994**, 64, 1842-1844	3.4	32
41	Electron mean free path in Be metal. *Physical Review B*, **1994**, 50, 16817-16823	3.3	11
40	Theories of impurity resistivity in two dimensions. *Journal of Physics Condensed Matter*, **1993**, 5, 335-344	1.8	
39	Free-polaron absorption. *Physical Review B*, **1993**, 48, 7043-7049	3.3	4
38	Temperature dependence of the transmittance, reflectance and absorption of optical films. *Thin Solid Films*, **1992**, 208, 96-99	2.2	3
37	Theories of impurity resistivity. *Journal of Physics Condensed Matter*, **1991**, 3, 1493-1504	1.8	4
36	Effects of electron-electron scattering on impurity resistivity. *Journal of Physics Condensed Matter*, **1991**, 3, 8425-8432	1.8	3
35	Intraband relaxation time in highly excited semiconductors. *Physical Review B*, **1991**, 43, 7136-7144	3.3	17
34	Temperature-dependent resistivity of heavily doped silicon and germanium. *Physical Review B*, **1990**, 41, 3060-3068	3.3	22

33	Tunneling current spectroscopy of electron subbands in n-type δ-doped silicon structures grown by molecular beam epitaxy. *Journal of Applied Physics*, **1990**, 67, 1962-1968	2.5	12
32	Electron-electron interactions and the bandwidth of metals. *Physical Review Letters*, **1989**, 62, 2718-2720	7.4	106
31	Optical free-carrier absorption of an electron-hole plasma in silicon. *Physical Review B*, **1989**, 39, 10825-10830	3.3	8
30	Generalized Drude approach to the conductivity relaxation time due to electron-hole collisions in optically excited semiconductors. *Physical Review B*, **1989**, 40, 12438-12440	3.3	29
29	Free-carrier absorption from Fibonacci sequences of delta -doped layers in silicon. *Physical Review B* , **1989**, 40, 6218-6221	3.3	3
28	Electrical characterization and subband structures in antimony δ-doped molecular beam epitaxy-silicon layers. *Thin Solid Films*, **1989**, 183, 331-338	2.2	11
27	Theoretical optical properties of polar semiconductors used as optical coatings for energy-efficient windows. *Thin Solid Films*, **1989**, 177, 69-75	2.2	15
26	Reactively sputtered ZnO: Al films for energy-efficient windows. *Thin Solid Films*, **1988**, 164, 381-386	2.2	63
25	Band-gap tailoring of ZnO by means of heavy Al doping. *Physical Review B*, **1988**, 37, 10244-10248	3.3	732
24	Dimensional crossover for a quasi-one-dimensional polaron. *Physical Review B*, **1988**, 37, 7079-7082	3.3	2
23	Self-energy corrections in photoemission of Na. *Physical Review B*, **1987**, 36, 4499-4502	3.3	67
22	Polaron in n dimensions. *Physical Review B*, **1987**, 36, 9059-9067	3.3	12
21	Dynamical conductivity in the infrared from impurity scattering in a polar semiconductor. *Physical Review B*, **1987**, 36, 1080-1089	3.3	34
20	Self-energy shifts in heavily doped, polar semiconductors. *Physical Review B*, **1987**, 36, 4878-4887	3.3	38
19	Theoretical predictions for the surface states on Ge(111)2 x 1: The degree of antibonding surface-state filling and relative shifts of the two surface-state bands as functions of doping level. *Physical Review B*, **1986**, 33, 2949-2952	3.3	3
18	Band-gap shifts in heavily p-type doped semiconductors of the zinc-blende and diamond type. *Physical Review B*, **1986**, 34, 5610-5620	3.3	67
17	Electron-hole liquid in layered InSe: Comparison of two- and three-dimensional excitonic states. *Physical Review B*, **1986**, 33, 8568-8581	3.3	19
16	Band-gap shifts in heavily doped n-type GaAs. *Physical Review B*, **1986**, 33, 8582-8586	3.3	63

15	Polarized hot-electron photoluminescence in highly doped GaAs. *Physical Review B*, **1986**, 34, 8696-8702	3.3	6
14	The zero-temperature d.c. conductivity versus density and the metal-insulator transition in some heavily doped semiconductor systems. *The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties*, **1985**, 52, 459-469		5
13	Very heavily doped semiconductors as a "nearly-free-electron-gas" system. *Solid-State Electronics*, **1985**, 28, 11-15	1.7	19
12	Bandgap widening in heavily doped oxide semiconductors used as transparent heat-reflectors. *Solar Energy Materials and Solar Cells*, **1985**, 12, 479-490		19
11	Effects of quantum confinement in a special GaAs field effect transistor: on the DC conductance in the regime of metallic transport. *Journal of Physics C: Solid State Physics*, **1985**, 18, 225-240		33
10	Bandgap Widening in Heavily Sn-Doped In2O3 **1985**, 1051-1054		1
9	Intervalley mixing versus disorder in heavily doped n-type silicon. *Physical Review B*, **1984**, 29, 5575-5580	3.3	32
8	Elementary excitations and quasi-two-dimensional behavior in a GaAs field-effect transistor. *Physical Review B*, **1984**, 30, 1016-1018	3.3	2
7	Band-gap widening in heavily Sn-doped In2O3. *Physical Review B*, **1984**, 30, 3240-3249	3.3	530
6	Bandgap Widening In Heavily Doped Oxide Semiconductors Used As Transparent Heat-Reflectors **1984**, 0502, 2		3
5	Theoretical high-stress optical birefringence and piezoresistance in heavily doped germanium. Arguments against band tailing. *Physical Review B*, **1983**, 27, 6234-6245	3.3	11
4	Band-gap narrowing in heavily doped many-valley semiconductors. *Physical Review B*, **1981**, 24, 1971-1986	3.3	397
3	Electron states in heavily doped semiconductors. *The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties*, **1981**, 43, 115-148		37
2	Electron states in heavily doped semiconductors. *The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties*, **1980**, 42, 751-754		2
1	Origin of negative magnetoresistance in heavily doped n-type silicon and germanium. *Physical Review B*, **1979**, 19, 6390-6396	3.3	8